

-50V/0.13A P-Channel Advanced Power Mosfet

Features

- Low $R_{DS(on)}$ @ $V_{GS}=-10V$
- 3.3V Logic Level Control
- Lead free in comply with EU RoHS 2011/65/EU directives

Mechanical Data

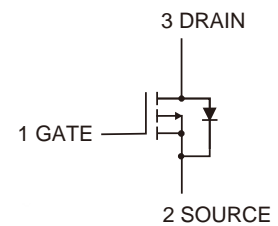
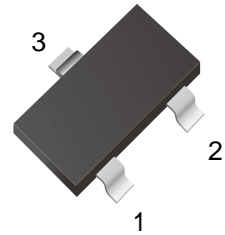
- Case: SOT-23
- Approx. Weight: 8.1mg

Application

- LED Lighting Application
- ON/OFF switch
- Networking

Ordering Information

Part Number	Marking	Shipping	Reel
LTM84P-TR3	PD	3000PCS Tape&Reel	7 inchs
LTM84P-TR12	PD	12000PCS Tape&Reel	13 inchs



Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ Typ	I_D Max
-50V	8Ω @ -10V	-0.13A
	10Ω @ -5V	

Maximum Ratings and Thermal Characteristics ($T_a=25$ unless otherwise noted)

Symbol	Parameter	Rating	Unit
Common Ratings ($T_A=25^{\circ}C$ Unless Otherwise Noted)			
V_{GS}	Gate-Source Voltage	±20	V
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	-50	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-50 ~ 150	°C
Mounted on Large Heat Sink			
I_{DM}	Pulse Drain Current Tested①	$T_A=25^{\circ}C$	-0.52 A
I_D	Continuous Drain Current	$T_A=25^{\circ}C$	-0.13 A
P_D	Maximum Power Dissipation	$T_A=25^{\circ}C$	0.225 W
		$T_A=70^{\circ}C$	0.15 W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	556	°C/W



Electrical Characteristics (Ta=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =-250μA	-50			V
I _{DSS}	Zero Gate Voltage Drain Current(T _A =25°C)	V _{DS} =-50V, V _{GS} =0V			-15	μA
	Zero Gate Voltage Drain Current(T _A =25°C)	V _{DS} =-25V, V _{GS} =0V			-0.1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V			±5	uA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.9	-1.6	-2	V
R _{DS(ON)}	Drain-Source On-State Resistance②	V _{GS} =-5V, I _D =-0.1A		5.8	10	Ω
R _{DS(ON)}	Drain-Source On-State Resistance②	V _{GS} =-10V, I _D =-0.1A		4.5	8	Ω
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
C _{iss}	Input Capacitance	V _{DS} =5V, V _{GS} =0V, f=1MHz		30		pF
C _{oss}	Output Capacitance			10		pF
C _{rss}	Reverse Transfer Capacitance			5		pF
Switching Characteristics						
t _{d(on)}	Turn on Delay Time	V _{DD} =-15V, I _D =-2.5A, R _L =50Ω,		2.5		ns
t _r	Turn on Rise Time			1		ns
t _{d(off)}	Turn Off Delay Time			16		ns
t _f	Turn Off Fall Time			8		ns
Source Drain Diode Characteristics						
I _{SD}	Source drain current(Body Diode)	T _A =25°C			-0.13	A
V _{SD}	Forward on voltage②	T _J =25°C, I _{SD} =0.13A, V _{GS} =0V			-2.2	V

Notes:

① Pulse width limited by maximum allowable junction temperature

② Pulse test ; Pulse width≤300μs, duty cycle≤2%.



Characteristic Curves

Fig1. Typical Output Characteristics

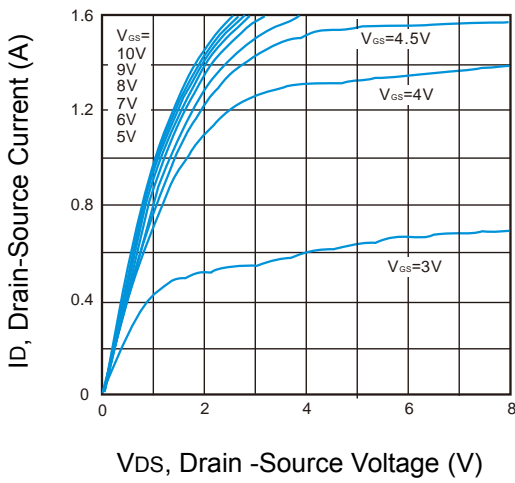


Fig2. Normalized Threshold Voltage Vs Temperature

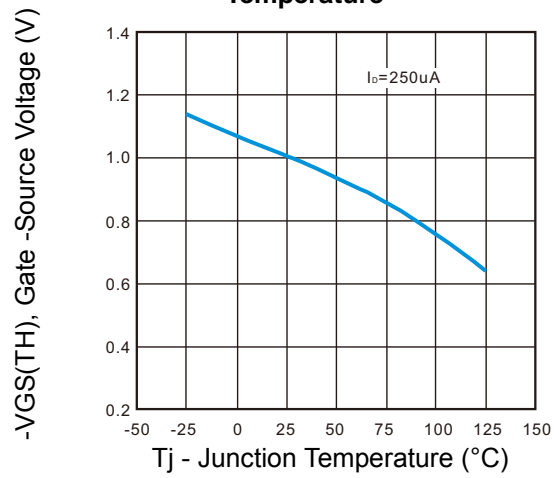


Fig3. Typical Transfer Characteristics

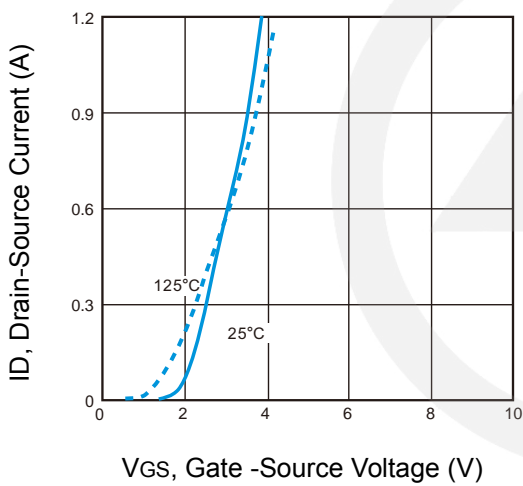


Fig4. Drain-Source Voltage vs Gate-Source Voltage

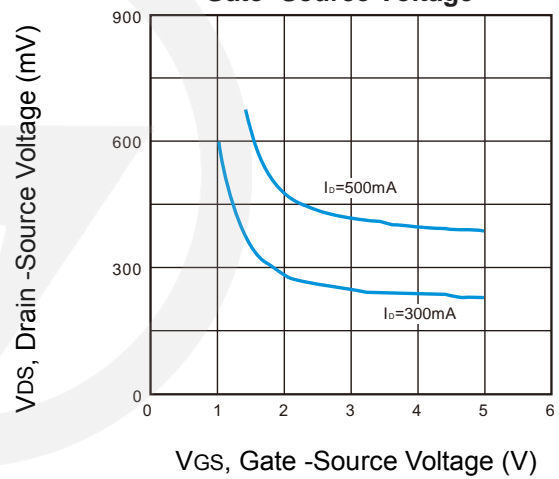


Fig5. Typical Source-Drain Diode Forward Voltage

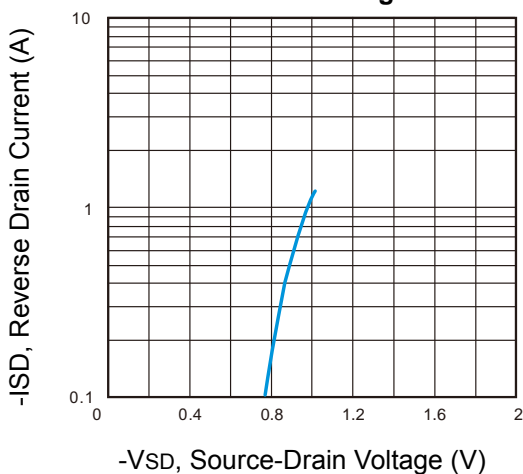


Fig6. Maximum Safe Operating Area

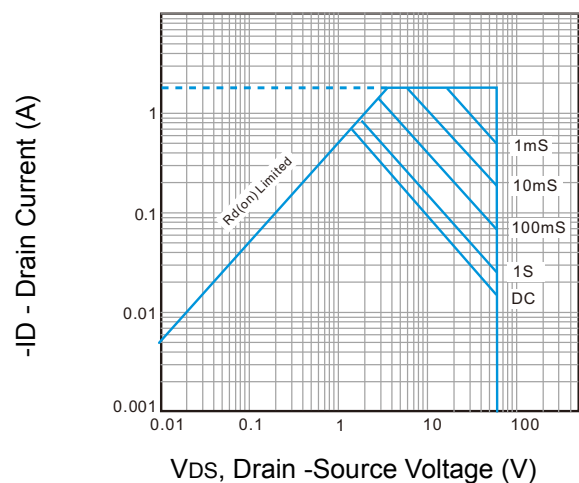




Fig7. Typical Capacitance Vs Drain-Source Voltage

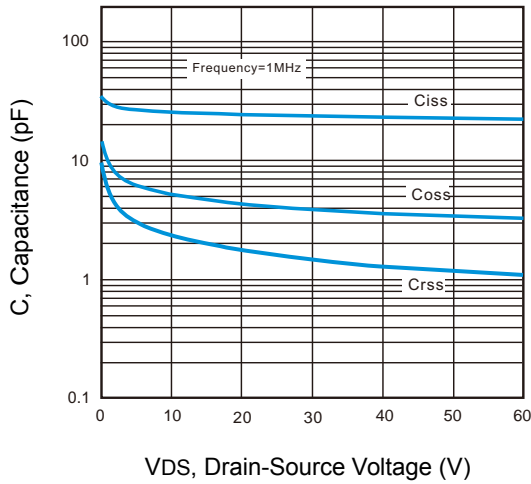
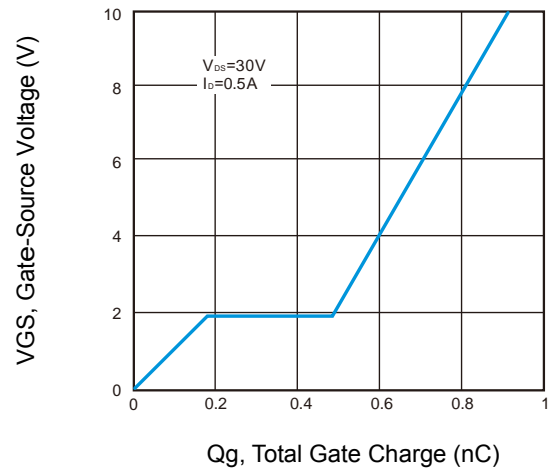
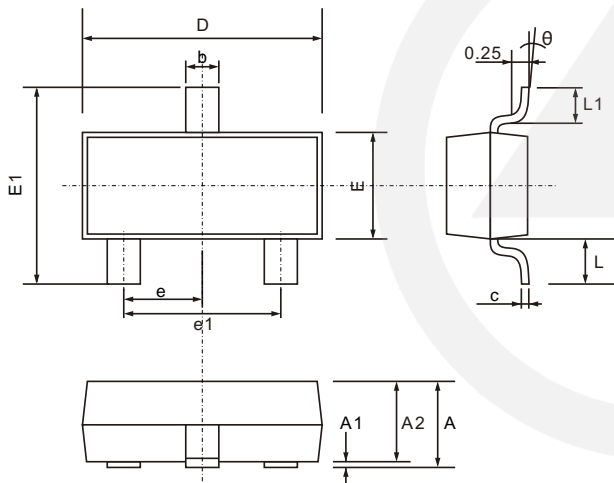


Fig8. Typical Gate Charge Vs Gate-Source Voltage



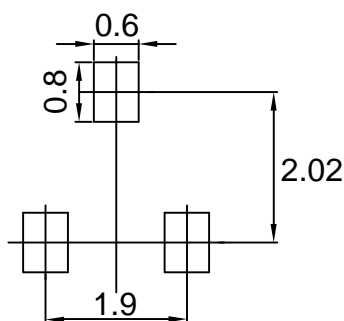
SOT-23 Package Outline

Unit : mm



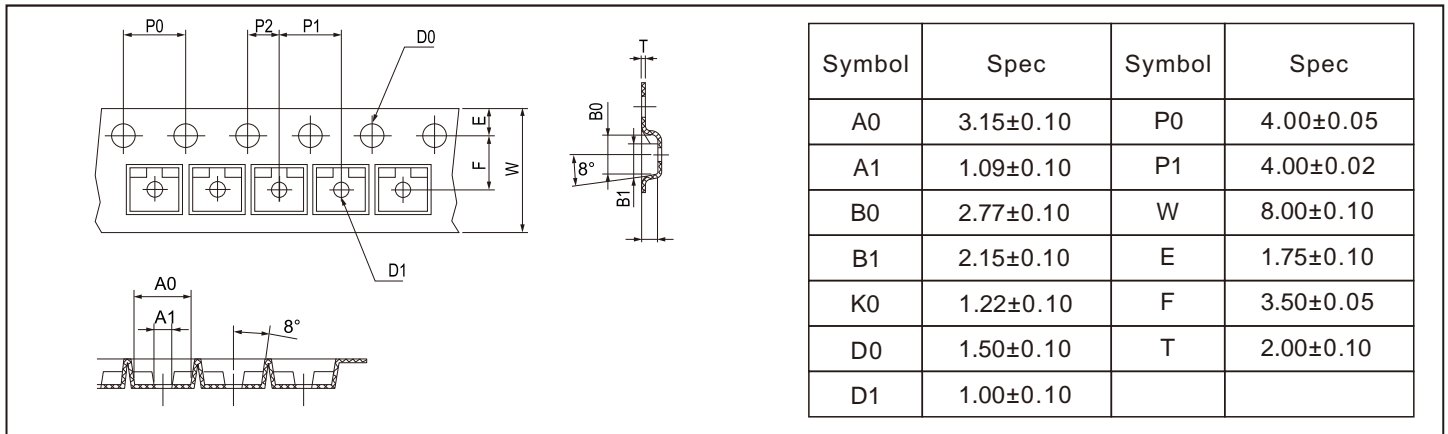
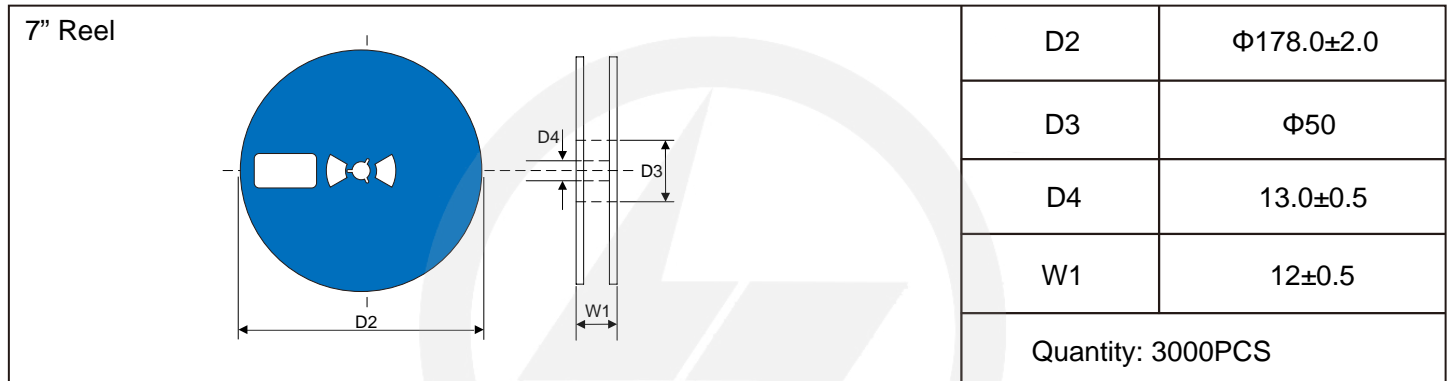
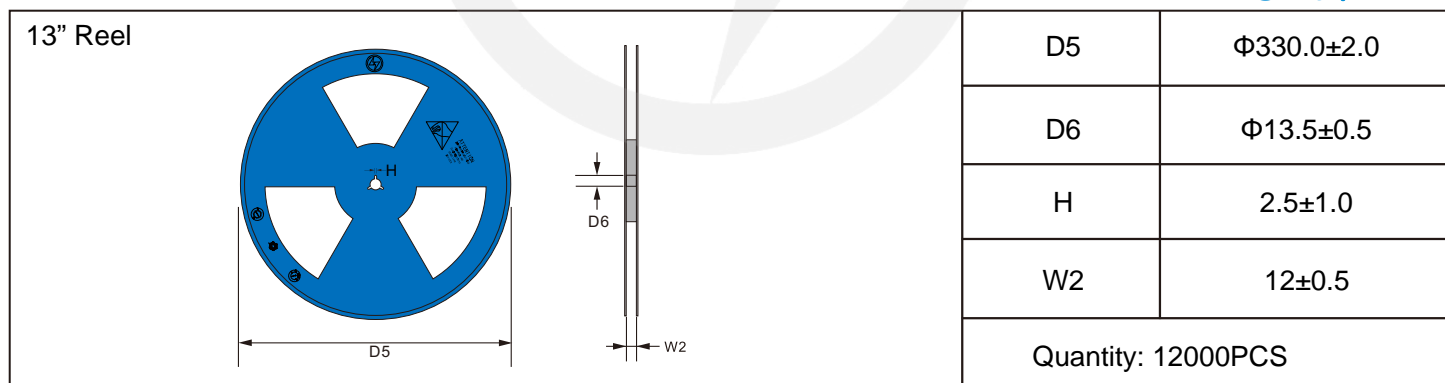
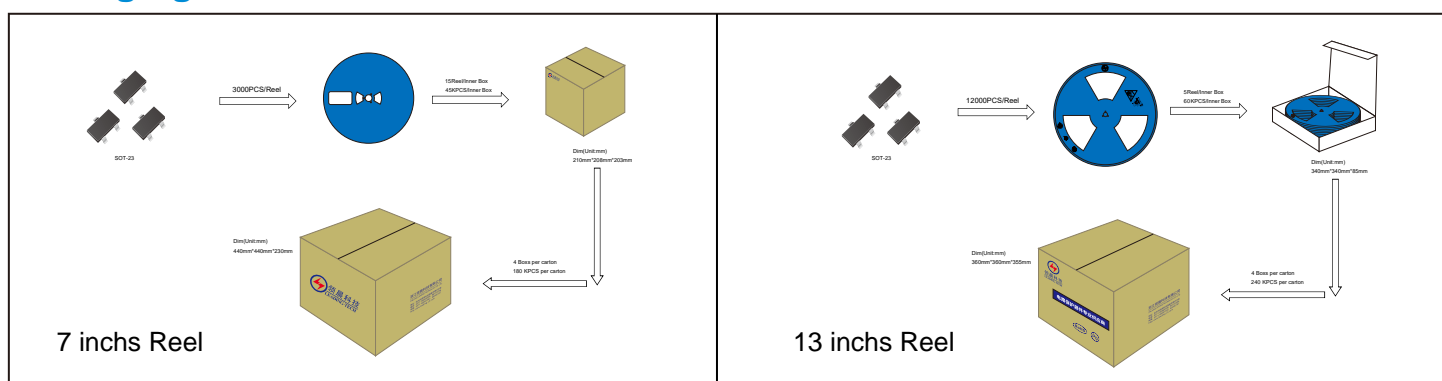
SYMBOL	DIMENSIONS	
	MIN.	MAX.
A	0.900	1.200
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.200
D	2.700	3.100
E	1.200	1.400
E1	2.200	2.600
e	0.950 TYP.	
e1	1.750	2.050
L	0.550 TYP.	
L1	0.300	0.500
θ	0°	8°

SOT-23 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05mm
3. The pad layout is for reference purpose only.

Carrier Tape Dimensions
Unit : mm

Reel Dimensions
Unit : mm

Reel Dimensions
Unit : mm

Packaging




Recommended Soldering Conditions



Recommended Conditions

Profile Feature	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	3°C/second max.
Preheat	
-Temperature Min ($T_{S\ min}$)	150°C
-Temperature Max ($T_{S\ max}$)	200°C
-Time (min to max) (t_s)	60-180 seconds
$T_{S\ max}$ to T_L	
-Ramp-up Rate	3°C/second max.
Time maintained above:	
-Temperature (T_L)	217°C
-Time (t_L)	60-150 seconds
Peak Temperature (T_P)	260°C
Time within 5°C of actual Peak Temperature (t_p)	20-40 seconds
Ramp-down Rate	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.

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Version Update Information

Series NO.	Enactment/Revision Date	Effective Date	Version	Revision Content	Revision Reason	Revision Person	Note
01	2024.3.18	2024.3.18	3.0	New file	/	Ding	
02	2025.06.16	2025.06.16	3.1	Update packaging information	/	Ding	
03	2026.03.05	2026.03.05	3.2	Package outline E1(max)=2.6mm	/	Ding	